PSMN4R3-100ES

N-channel 100 V 4.3 mΩ standard level MOSFET in I2PAK

Rev. 1 — 31 October 2011 **Product data sheet**

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

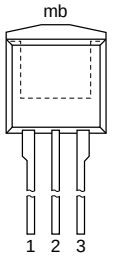
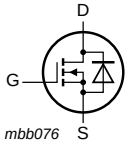
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	100	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1	[1]	-	-	120	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	-	338	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 100$ °C; see Figure 12; see Figure 13		-	6.6	7.8	mΩ
		$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 13	[2]	-	3.7	4.3	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 75$ A; $V_{DS} = 50$ V; see Figure 14; see Figure 15		-	49	-	nC
$Q_{G(tot)}$	total gate charge			-	170	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 120$ A; $V_{sup} \leq 100$ V; $R_{GS} = 50$ Ω; Unclamped		-	-	537	mJ

[1] Continuous current limited by package

[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT226 (I2PAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

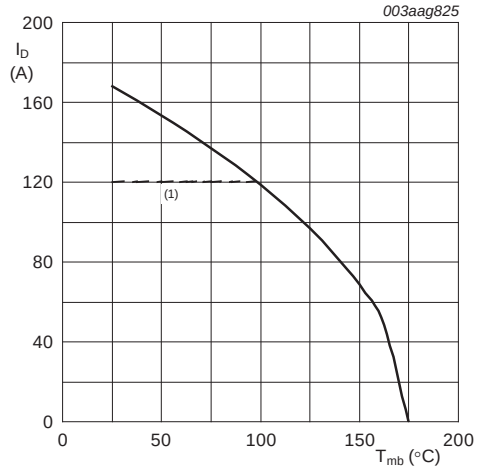
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

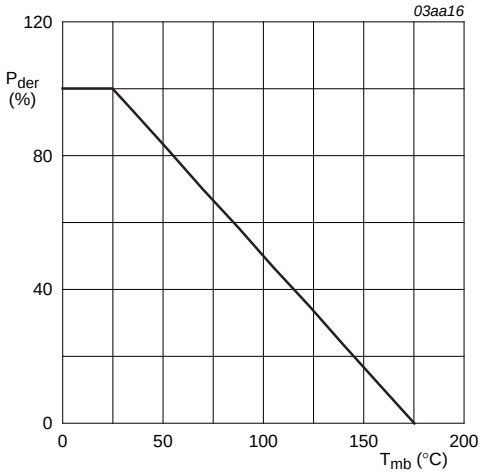
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_j = 100$ °C; see Figure 1		-	119	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; see Figure 3		-	673	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	338	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	673	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 120$ A; $V_{sup} \leq 100$ V; $R_{GS} = 50$ Ω; Unclamped		-	537	mJ

[1] Continuous current limited by package



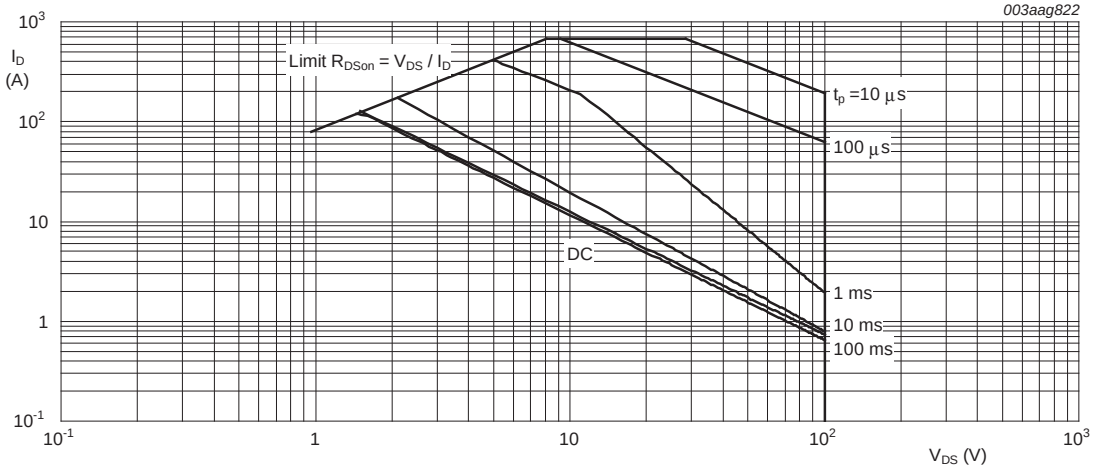
$V_{GS} \geq 10\,V$; (1) Capped at 120A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C$; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

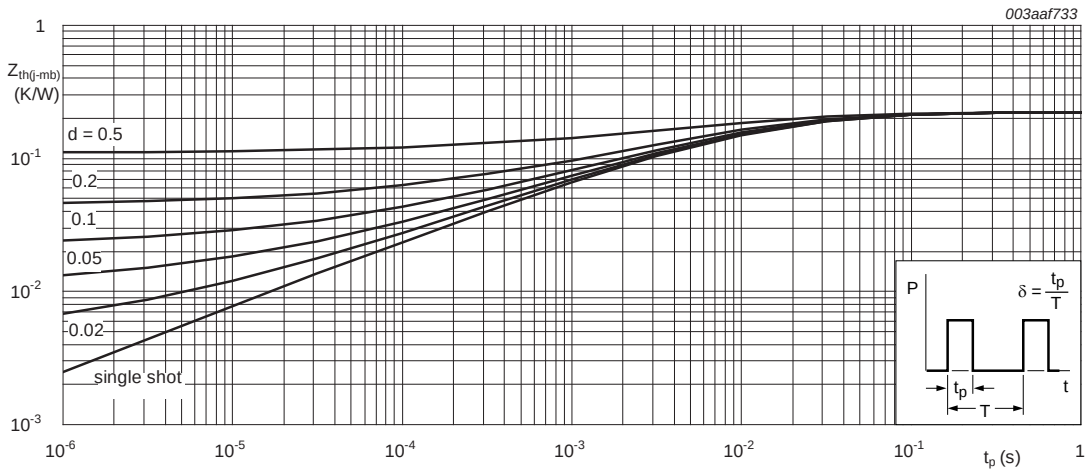


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

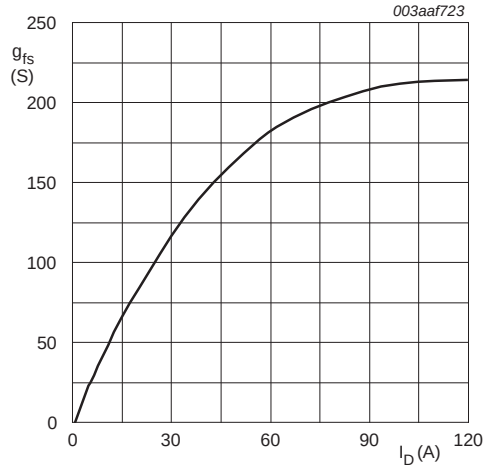
Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10		-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 11; see Figure 10		2	3	4	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.08	10	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12; see Figure 13		-	10.4	12	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13		-	6.6	7.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13	[1]	-	3.7	4.3	mΩ
R_G	gate resistance	f = 1 MHz		-	0.9	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 75 A; V_{DS} = 50 V; V_{GS} = 10 V; see Figure 14; see Figure 15		-	170	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	140	-	nC
Q_{GS}	gate-source charge	I_D = 75 A; V_{DS} = 50 V; V_{GS} = 10 V; see Figure 14; see Figure 15		-	48	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	31	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	17.3	-	nC
Q_{GD}	gate-drain charge			-	49	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V_{DS} = 50 V; see Figure 14; see Figure 15		-	5.1	-	V
C_{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 16		-	9900	-	pF
C_{oss}	output capacitance			-	660	-	pF
C_{rss}	reverse transfer capacitance			-	381	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; R_L = 0.67 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 4.7 Ω; I_D = 75 A; T_j = 25 °C		-	45	-	ns
t_r	rise time			-	91	-	ns
$t_{d(off)}$	turn-off delay time			-	122	-	ns
t_f	fall time			-	63	-	ns

Table 6. Characteristics *…continued*

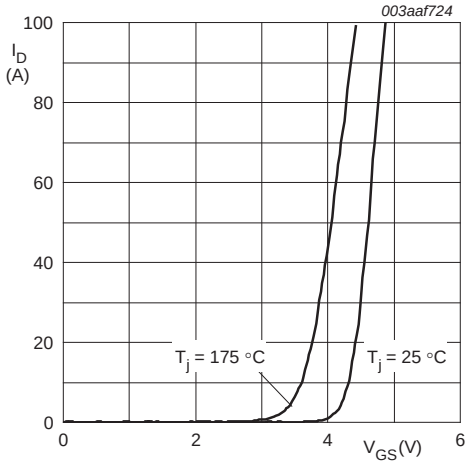
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 17	-	0.8	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V	-	75	-	ns
Q_r	recovered charge		-	235	-	nC

[1] Measured 3 mm from package.



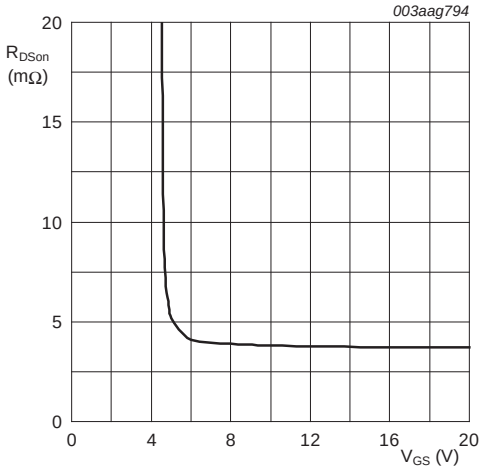
$T_j = 25\ °C; V_{DS} = 25\ V$

Fig 5. Forward transconductance as a function of drain current; typical values



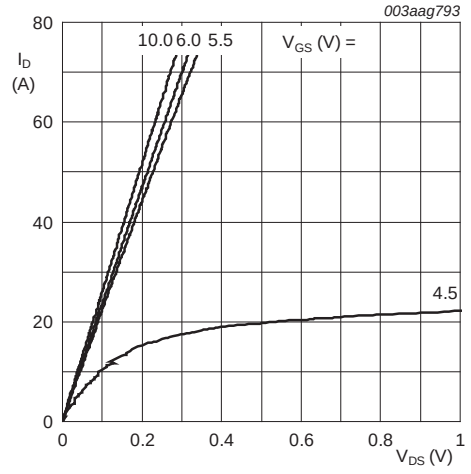
$V_{DS} = 25\ V$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



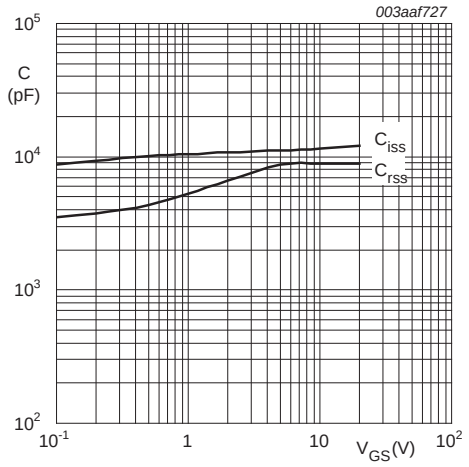
$T_j = 25°C;\ I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



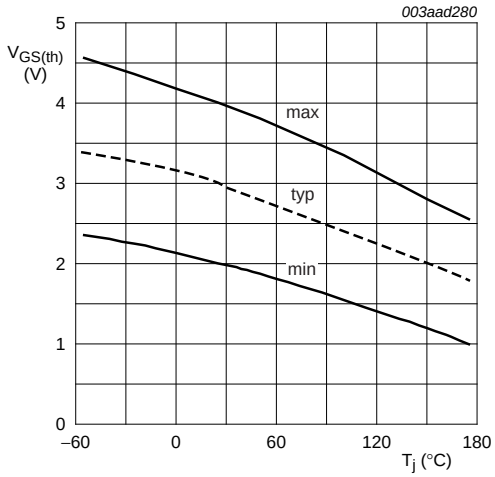
$T_j = 25°C$

Fig 8. Output characteristics; drain current as a function of drain-source voltage; typical values



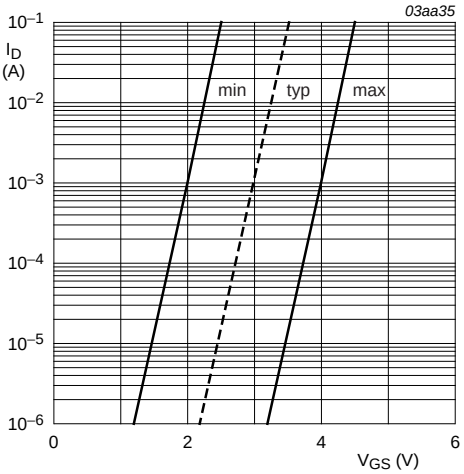
f = 1 MHz; V_{DS} = 0 V;

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



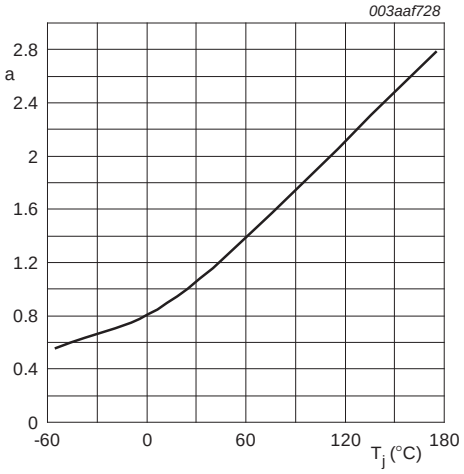
I_D = 1 mA; V_{DS} = V_{GS}

Fig 10. Gate-source threshold voltage as a function of junction temperature



$T_j = 25\,°C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

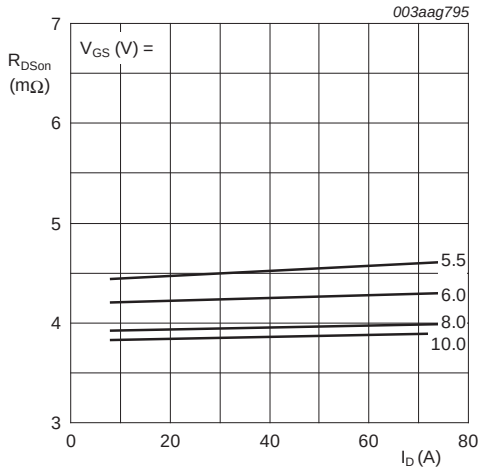


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

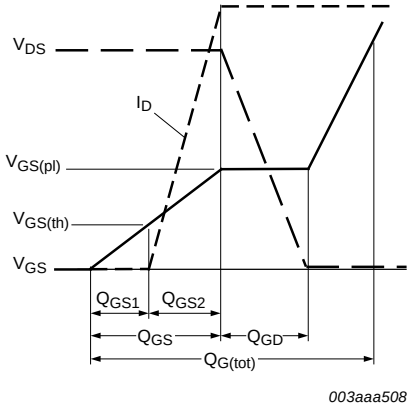


Fig 14. Gate charge waveform definitions

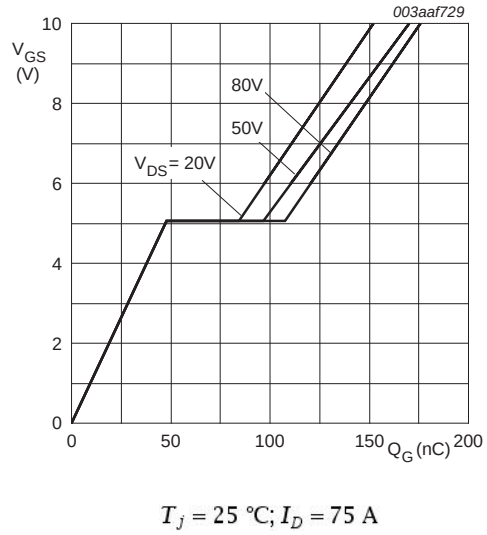


Fig 15. Gate-source voltage as a function of gate charge; typical values

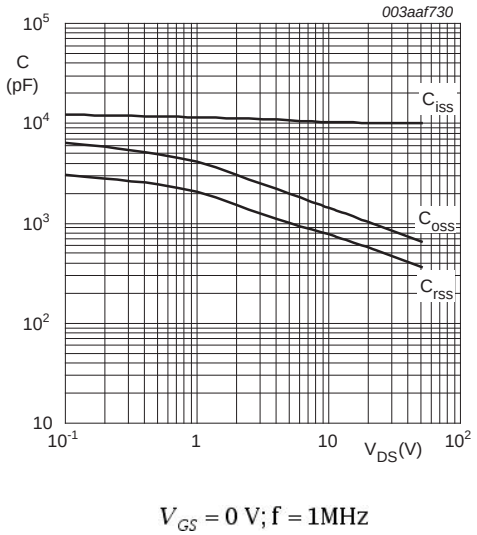
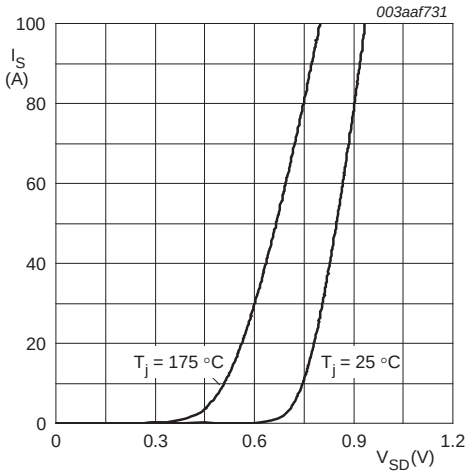


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

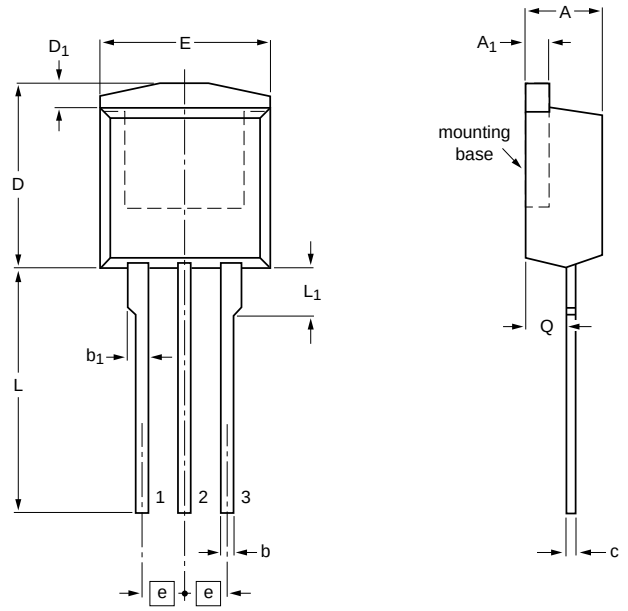


$V_{GS} = 0$ V

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262 **SOT226**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D max	D_1	E	e	L	L_1	Q
mm	4.5 4.1	1.40 1.27	0.85 0.60	1.3 1.0	0.7 0.4	11	1.6 1.2	10.3 9.7	2.54	15.0 13.5	3.30 2.79	2.6 2.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT226		TO-262				~~06-02-14~~ 09-08-25

Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R3-100ES v.1	20111031	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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10. Contact information

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